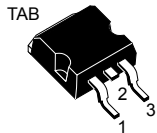
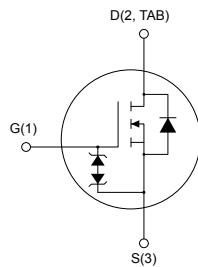


N-channel 600 V, 68 mΩ typ., 36 A, MDmesh M6 Power MOSFET in a D²PAK package


 D²PAK


AM01475V1



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STB46N60M6	600 V	80 mΩ	36 A

- Reduced switching losses
- Lower R_{DS(on)} per area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications
- LLC converters
- Boost PFC converters

Description

The new MDmesh M6 technology incorporates the most recent advancements to the well-known and consolidated MDmesh family of SJ MOSFETs. STMicroelectronics builds on the previous generation of MDmesh devices through its new M6 technology, which combines excellent R_{DS(on)} per area improvement with one of the most effective switching behaviors available, as well as a user-friendly experience for maximum end-application efficiency.

Product status link

[STB46N60M6](#)

Product summary

Order code	STB46N60M6
Marking	46N60M6
Package	D ² PAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_{case} = 25\text{ }^\circ\text{C}$	36	A
	Drain current (continuous) at $T_{case} = 100\text{ }^\circ\text{C}$	23	
$I_D^{(1)}$	Drain current (pulsed)	126	A
P_{TOT}	Total power dissipation at $T_{case} = 25\text{ }^\circ\text{C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	100	
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 36\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
3. $V_{DS} \leq 480\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	30	$^\circ\text{C}/\text{W}$

1. When mounted on 1 a inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_{Jmax})	5.2	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	760	mJ

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$			1	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$, $T_{\text{case}} = 125\text{ °C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 25\text{ V}$			± 5	μA
$V_{\text{GS}(\text{th})}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{\text{DS}(\text{on})}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 18\text{ A}$		68	80	$\text{m}\Omega$

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{\text{DS}} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	2340	-	pF
C_{oss}	Output capacitance		-	147	-	
C_{riss}	Reverse transfer capacitance		-	3.7	-	
$C_{\text{oss eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }480\text{ V}$, $V_{\text{GS}} = 0\text{ V}$	-	339	-	pF
R_{G}	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_{\text{D}} = 0\text{ A}$	-	1.6	-	Ω
Q_{g}	Total gate charge	$V_{\text{DD}} = 480\text{ V}$, $I_{\text{D}} = 36\text{ A}$, $V_{\text{GS}} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	53.5	-	nC
Q_{gs}	Gate-source charge		-	15.5	-	
Q_{gd}	Gate-drain charge		-	23.5	-	

1. $C_{\text{oss eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d}(\text{on})}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$, $I_{\text{D}} = 18\text{ A}$, $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$	-	20	-	ns
t_{r}	Rise time		-	15.5	-	
$t_{\text{d}(\text{off})}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	48.4	-	
t_{f}	Fall time		-	8.5	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		36	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		126	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 36\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 36\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	267		ns
Q_{rr}	Reverse recovery charge		-	2.8		μC
I_{RRM}	Reverse recovery current		-	20.8		A
t_{rr}	Reverse recovery time	$I_{SD} = 36\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	440		ns
Q_{rr}	Reverse recovery charge		-	5.8		μC
I_{RRM}	Reverse recovery current		-	26.4		A

1. Pulse width is limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

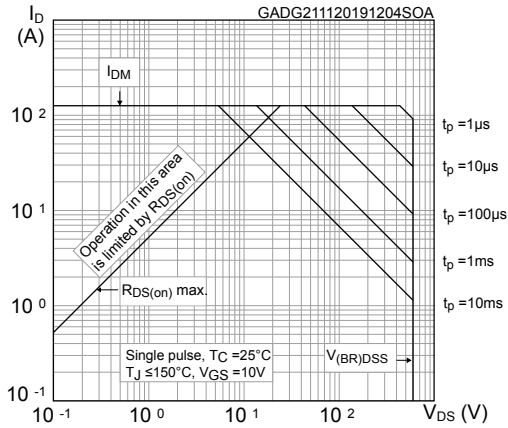


Figure 2. Maximum transient thermal impedance

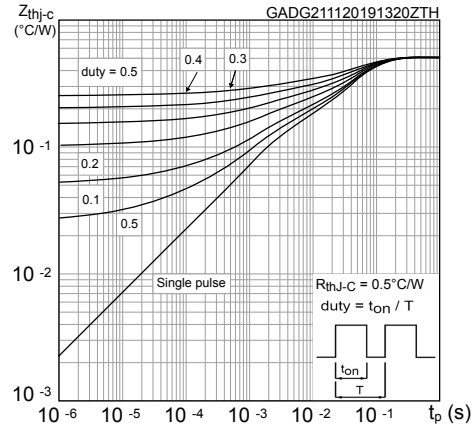


Figure 3. Typical output characteristics

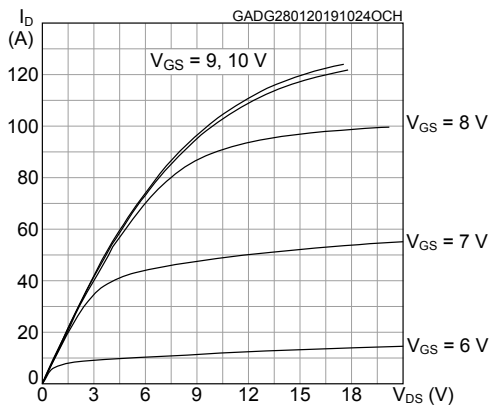


Figure 4. Typical transfer characteristics

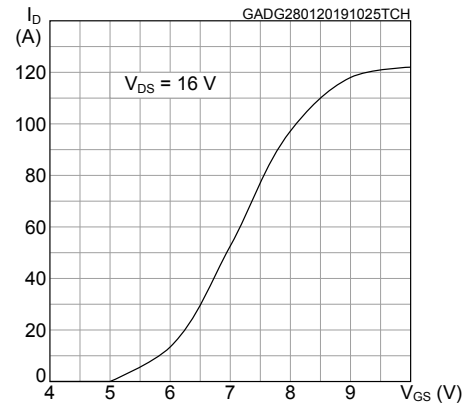


Figure 5. Typical gate charge characteristics

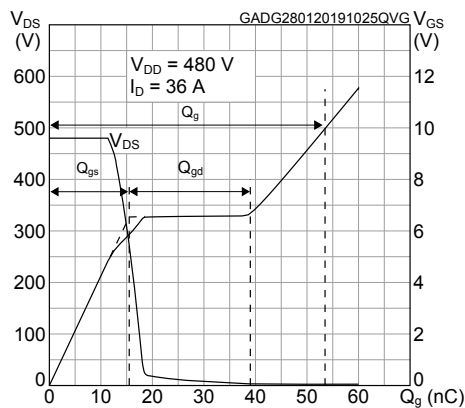


Figure 6. Typical drain-source on-resistance

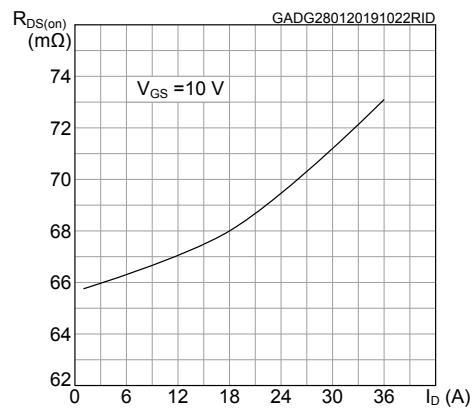


Figure 7. Typical capacitance characteristics

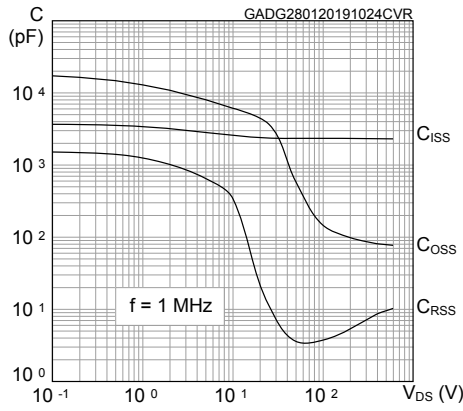


Figure 8. Normalized gate threshold vs temperature

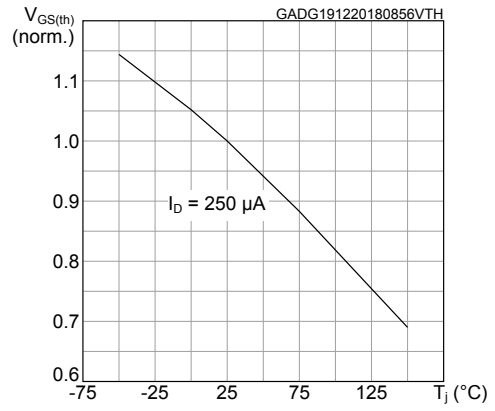


Figure 9. Normalized on-resistance vs temperature

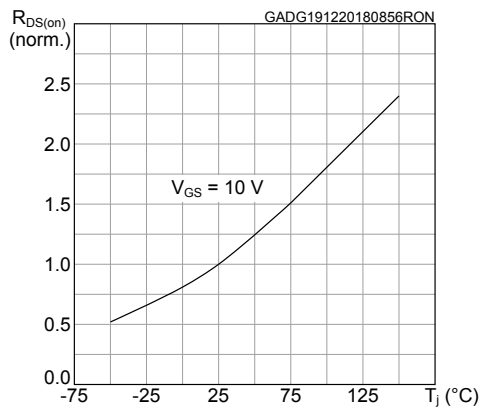


Figure 10. Normalized breakdown voltage vs temperature

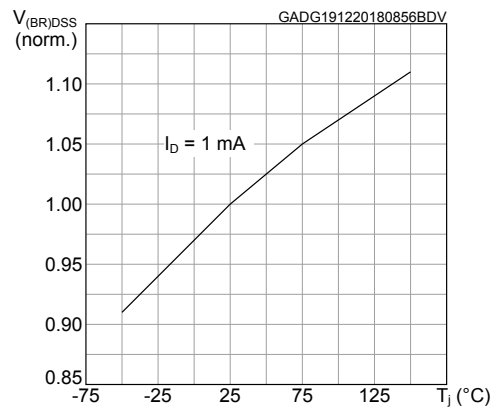


Figure 11. Typical output capacitance stored energy

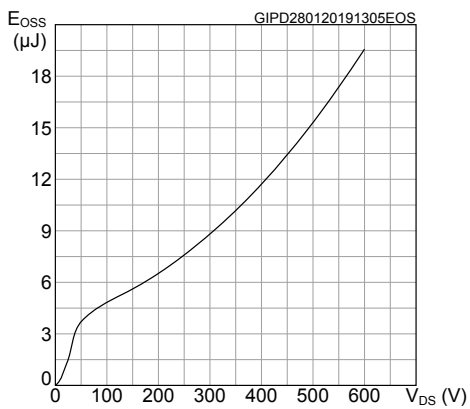
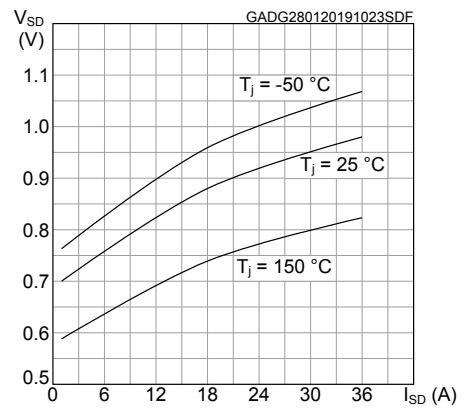
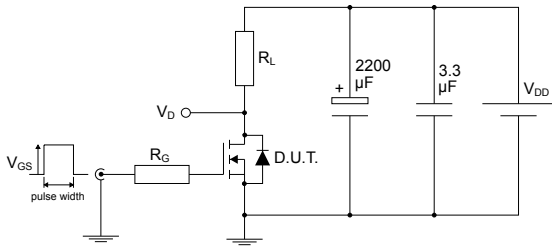


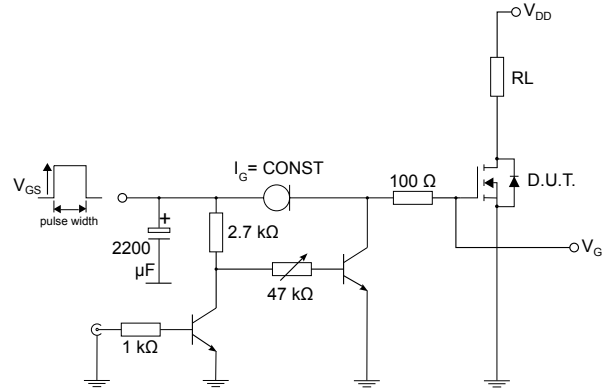
Figure 12. Typical reverse diode forward characteristics



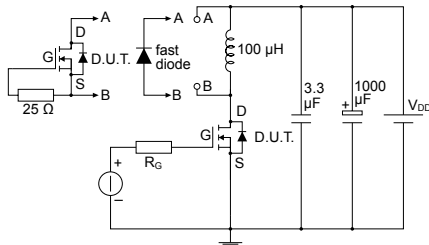
3 Test circuits

Figure 13. Test circuit for resistive load switching times


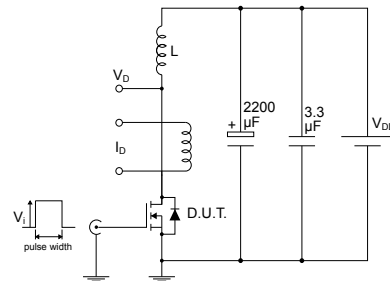
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Figure 14. Test circuit for gate charge behavior


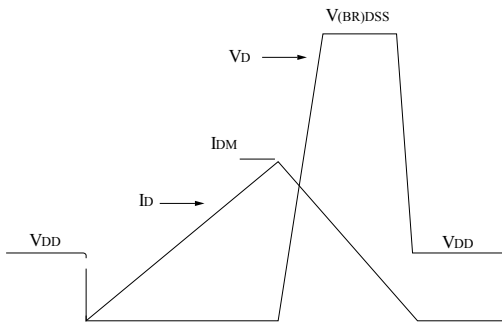
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Figure 15. Test circuit for inductive load switching and diode recovery times


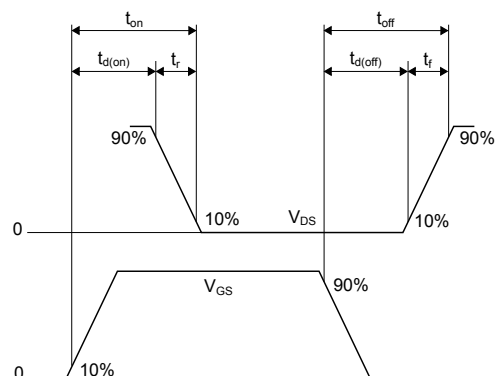
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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


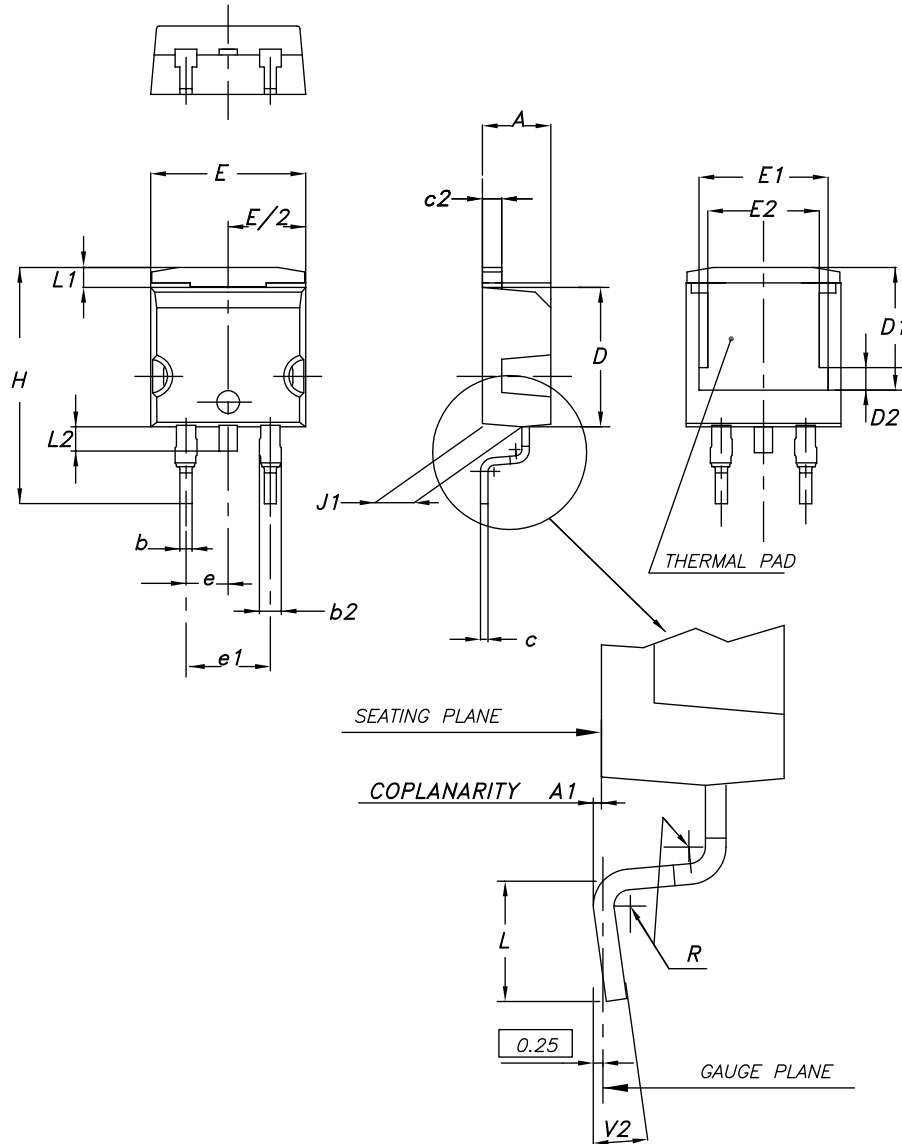
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A2 package information

Figure 19. D²PAK (TO-263) type A2 package outline



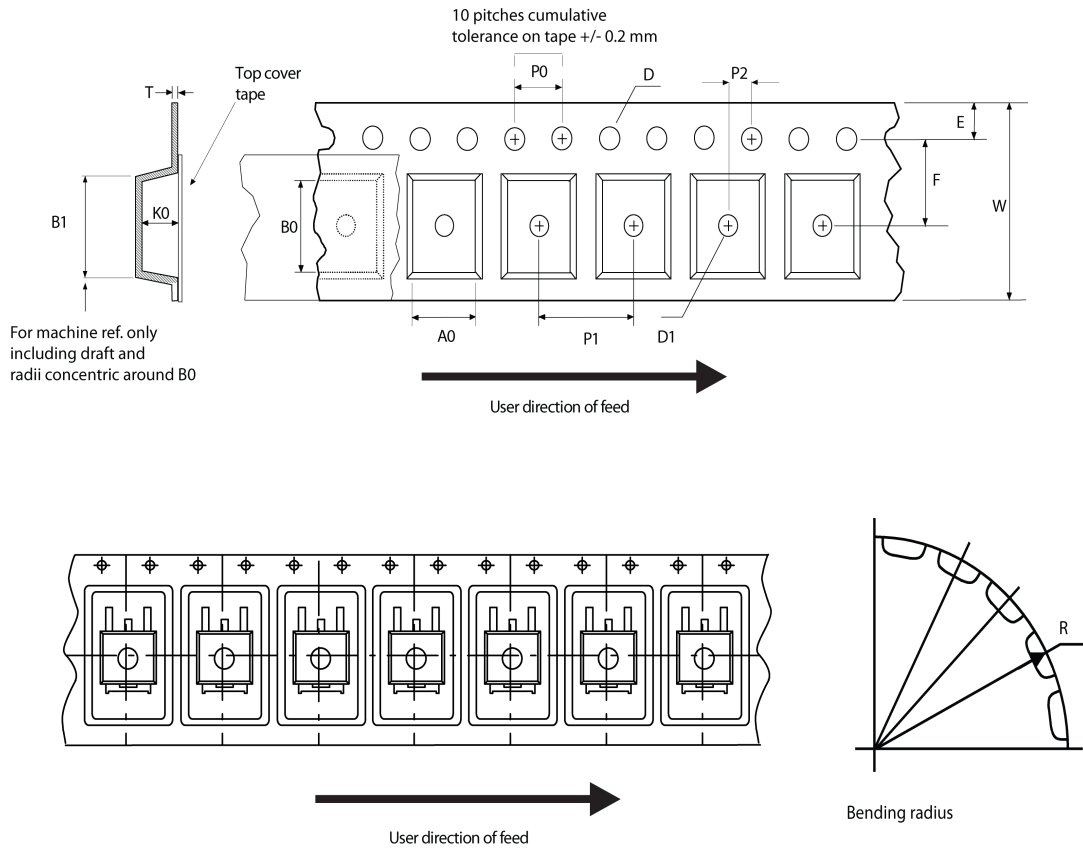
0079457_A2_26

Table 8. D²PAK (TO-263) type A2 package mechanical data

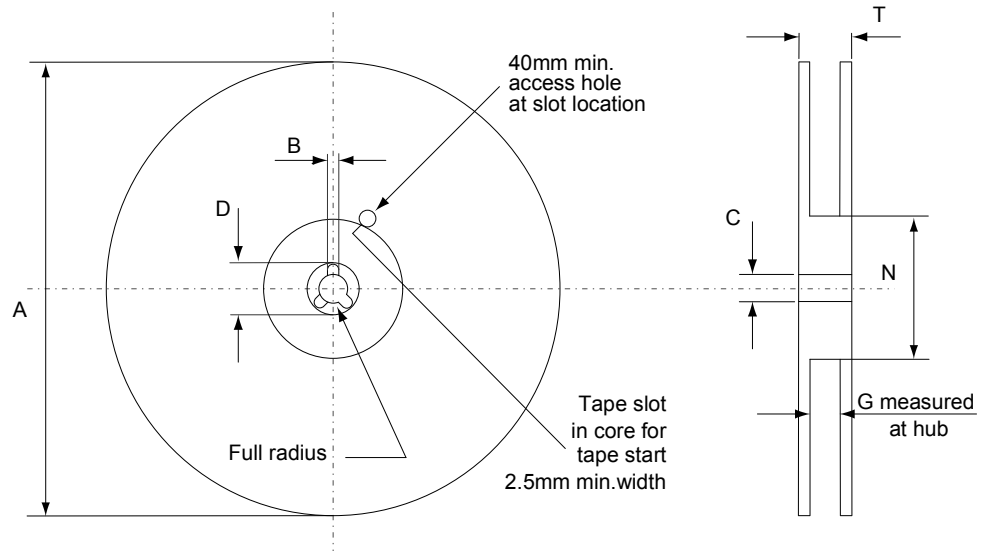
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.70	8.90	9.10
E2	7.30	7.50	7.70
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

4.2 D²PAK packing information

Figure 20. D²PAK tape outline



AM08852v1

Figure 21. D²PAK reel outline


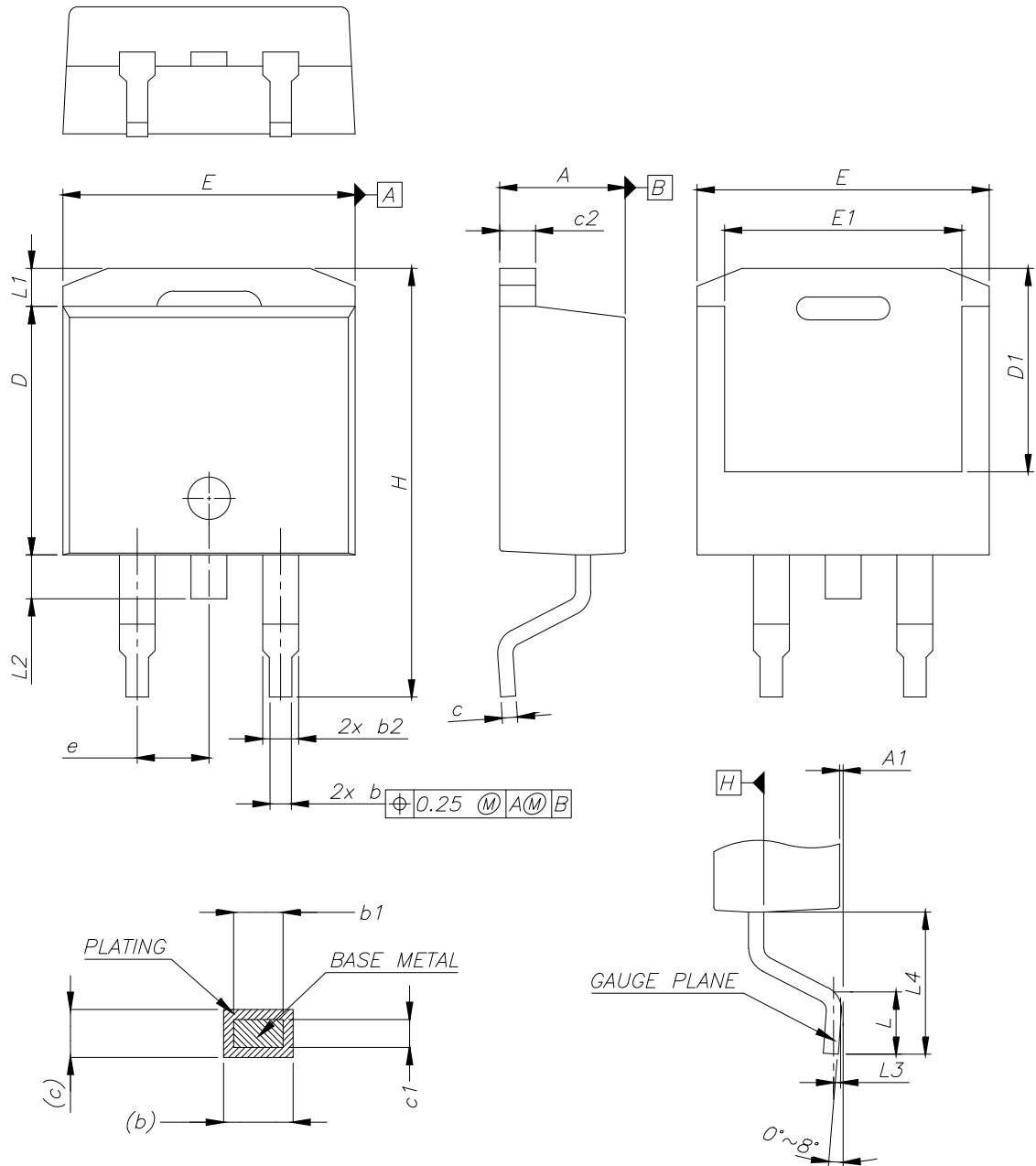
AM06038v1

Table 9. D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1	Base quantity		
P1	11.9	12.1			
P2	1.9	2.1	Bulk quantity		
R	50				
T	0.25	0.35			
W	23.7	24.3			

4.3 D²PAK (TO-263) type B package information

Figure 22. D²PAK (TO-263) type B package outline

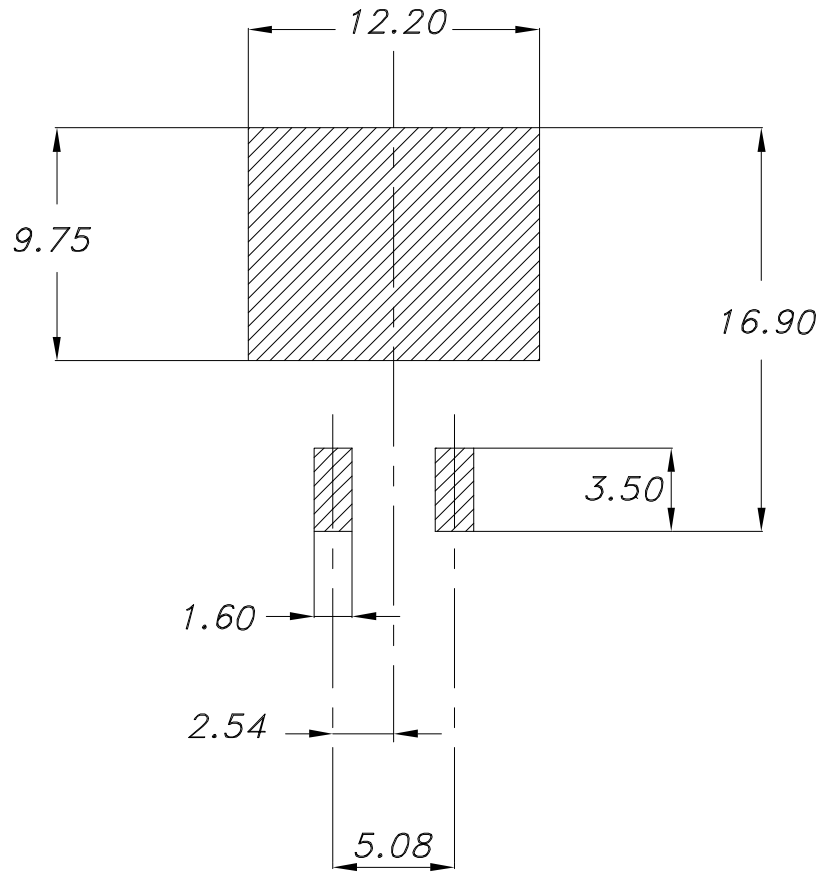


0079457_26_B

Table 10. D²PAK (TO-263) type B mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.36		4.56
A1	0		0.25
b	0.70		0.90
b1	0.51		0.89
b2	1.17		1.37
c	0.38		0.694
c1	0.38		0.534
c2	1.19		1.34
D	8.60		9.00
D1	6.90		7.50
E	10.15		10.55
E1	8.10		8.70
e	2.54 BSC		
H	15.00		15.60
L	1.90		2.50
L1			1.65
L2			1.78
L3		0.25	
L4	4.78		5.28

Figure 23. D²PAK (TO-263) recommended footprint (dimensions are in mm)



Footprint_26

4.4 D²PAK type B packing information

Figure 24. D²PAK type B tape outline

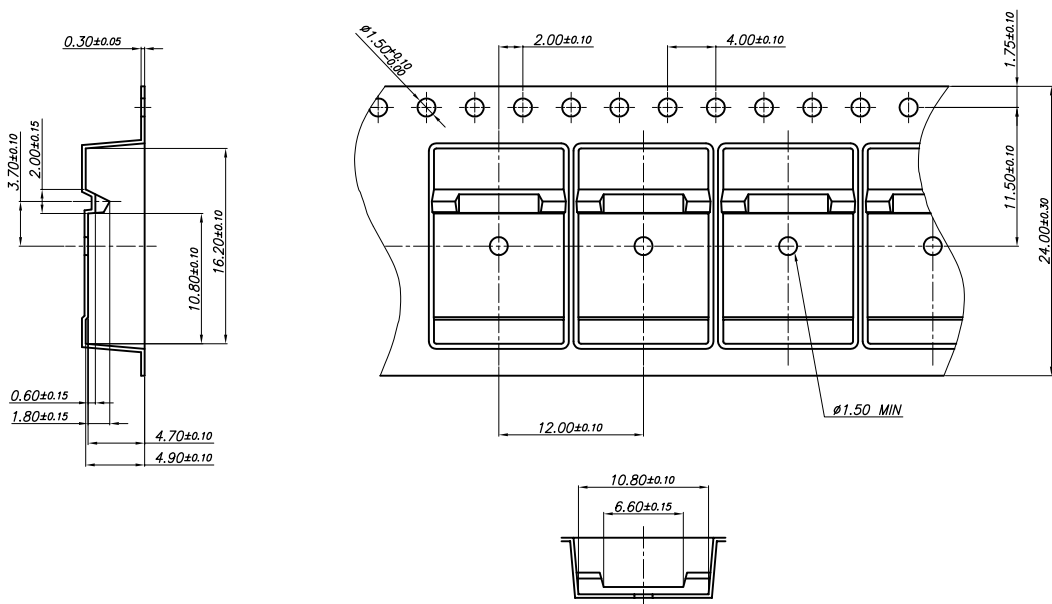
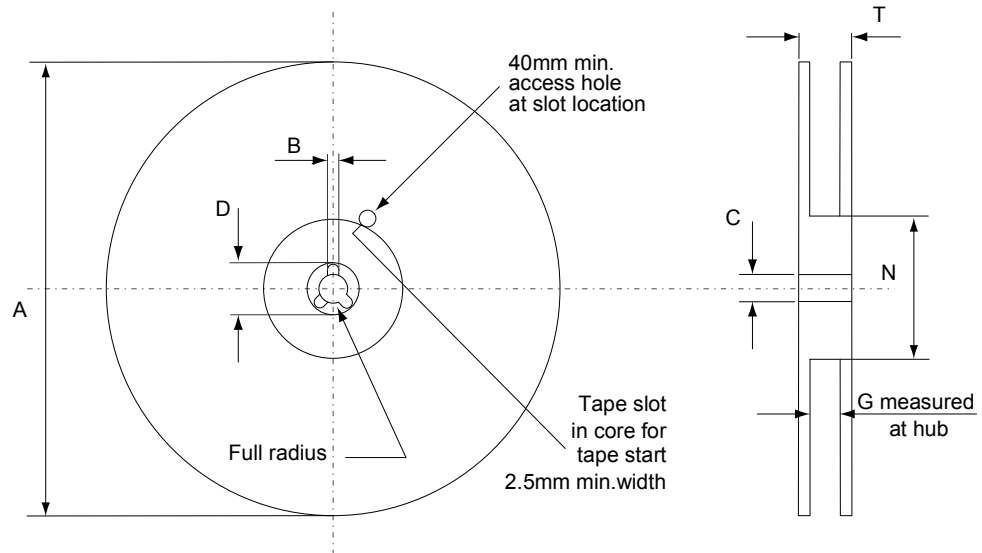


Figure 25. D²PAK type B reel outline



AM06038v1

Table 11. D²PAK type B reel mechanical data

Dim.	mm	
	Min.	Max.
A		330
B	1.5	
C	12.8	13.2
D	20.2	
G	24.4	26.4
N	100	
T		30.4

Revision history

Table 12. Document revision history

Date	Version	Changes
20-Mar-2019	1	First release.
25-Nov-2019	2	Updated Table 3. Avalanche characteristics , Section 2 Electrical characteristics and Section 2.1 Electrical characteristics (curves) . Minor text changes.

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